



高共模电压差动放大器

特性

- 共模电压范围: **$\pm 275\text{ V}$**
- 最小 **CMRR**: -40°C 至 125°C 时为 **90 dB**
- **DC** 规范
 - 最大偏移电压: **1100 μV**
 - 最大偏移电压漂移: **15 $\mu\text{V}/^{\circ}\text{C}$**
 - 最大增益误差: **0.02%**
 - 最大增益漂移误差: **10 ppm/ $^{\circ}\text{C}$**
 - 最大增益非线性值: **0.001% FSR**
- **AC** 性能:
 - 带宽: **500 kHz**
 - 典型转换率: **5 V/ μs**
- 宽电源电压范围: **$\pm 2.0\text{ V}$ 至 $\pm 18\text{ V}$**
 - 最大静态电流: **900 μA**
 - **$\pm 15\text{-V}$** 电源的输出摆幅: **$\pm 13.5\text{ V}$**
- 输入保护
 - 共模电压: **$\pm 500\text{ V}$**
 - 差分电压: **$\pm 500\text{ V}$**

应用

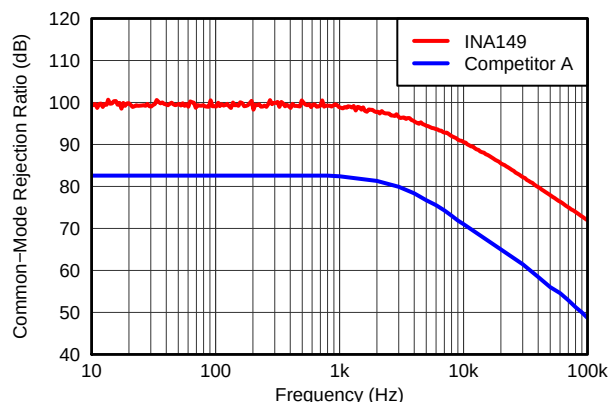
- 高压电流感应
- 电池电压监视
- 电源电流监视
- 电机控制
- 隔离电路的替代产品

说明

INA149 是一款高精度单位增益差动放大器，此放大器具有很高的输入共模电压范围。它是一款包含有高精度运算放大器和集成薄膜电阻器网路的单一单片器件。在共模信号电压高达 $\pm 275\text{ V}$ 时，INA149 可以准确测量较小的差分电压。INA149 输入受到最高 500 V 的瞬时共模电压或者的差分负载的保护。

在很多无需电流隔离的应用中，INA149 可以取代隔离放大器。此功能可以省去昂贵的隔离的输入端电源并去除相关纹波、噪音和静态电流。INA149 出色的 0.0005% 非线性和 500-kHz 带宽特性使之优于传统隔离放大器。

INA149 与 INA117-和 INA148-类型高共模电压放大器引脚兼容并且提供优于上述两设备的性能。INA149 采用 SOIC-8 封装，额定拓展工业工作温度范围为 -40°C 至 $+125^{\circ}\text{C}$ 。



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

PACKAGE/ORDERING INFORMATION⁽¹⁾

PRODUCT	PACKAGE-LEAD	PACKAGE DESIGNATOR	PACKAGE MARKING
INA149	SOIC-8	D	INA149A

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or visit the device product folder at www.ti.com.

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Over operating free-air temperature range, unless otherwise noted.

		INA149	UNIT
Supply voltage	(V+) – (V–)	40	V
Input voltage range	Continuous	300	V
Common-mode and differential, 10 s		500	V
Maximum Voltage on REF _A and REF _B		(V–) – 0.3 to (V+) + 0.3	V
Input current on any input pin ⁽²⁾		10	mA
Output short-circuit current duration		Indefinite	
Operating temperature range		–55 to +150	°C
Storage temperature range		–65 to +150	°C
Junction temperature		+150	°C
ESD rating	Human body model (HBM)	1500	V
	Charged device model (CDM)	1000	V
	Machine model (MM)	100	V

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
- (2) REF_A and REF_B are diode clamped to the power-supply rails. Signals applied to these pins that can swing more than 0.3 V beyond the supply rails should be limited to 10 mA or less.

ELECTRICAL CHARACTERISTICS: V+ = +15 V and V– = –15 V

At $T_A = +25^{\circ}\text{C}$, $R_L = 2\text{ k}\Omega$ connected to ground, and $V_{CM} = \text{REF}_A = \text{REF}_B = \text{GND}$, unless otherwise noted.

PARAMETER	TEST CONDITIONS	INA149			UNIT
		MIN	TYP	MAX	
GAIN					
Initial	V _{OUT} = ±10.0 V	1			V/V
Gain error	V _{OUT} = ±10.0 V	±0.005		±0.02	%FSR
Gain	vs temperature, T _A = −40°C to +125°C	±1.5		±10	ppm/°C
Nonlinearity		±0.0005		±0.001	%FSR
OFFSET VOLTAGE					
Initial offset		350		1100	μV
	vs temperature, T _A = −40°C to +125°C	3		15	μV/°C
	vs supply (PSRR), V _S = ±2 V to ±18 V	90	120		dB
INPUT					
Impedance	Differential	800			kΩ
	Common-mode	200			kΩ
Voltage range	Differential	−13.5		13.5	V
	Common-mode	−275		275	V
Common-mode rejection (CMRR)	At dc, V _{CM} = ±275 V	90	100		dB
	vs temperature, T _A = −40°C to +125°C, at dc	90			dB
	At ac, 500 Hz, V _{CM} = 500 V _{PP}	90			dB
	At ac, 1 kHz, V _{CM} = 500 V _{PP}		90		dB
OUTPUT					
Voltage range		−13.5		13.5	V
Short-circuit current		±25			mA
Capacitive load drive	No sustained oscillations	10			nF
OUTPUT NOISE VOLTAGE					
0.01 Hz to 10 Hz		20			μV _{PP}
10 kHz		550			nV/√Hz
DYNAMIC RESPONSE					
Small-signal bandwidth		500			kHz
Slew rate	V _{OUT} = ±10-V step	1.7	5		V/μs
Full-power bandwidth	V _{OUT} = 20 V _{PP}	32			kHz
Settling time	0.01%, V _{OUT} = 10-V step	7			μs
POWER SUPPLY					
Voltage range		±2		±18	V
Quiescent current	V _S = ±18 V, V _{OUT} = 0 V	810		900	μA
	vs temperature, T _A = −40°C to +125°C			1.1	mA
TEMPERATURE RANGE					
Specified		−40		+125	°C
Operating		−55		+150	°C
Storage		−65		+150	°C

ELECTRICAL CHARACTERISTICS: $V_+ = 5\text{ V}$ and $V_- = 0\text{ V}$

At $T_A = +25^\circ\text{C}$, $R_L = 2\text{ k}\Omega$ connected to 2.5 V , and $V_{CM} = \text{REF}_A = \text{REF}_B = 2.5\text{ V}$, unless otherwise noted.

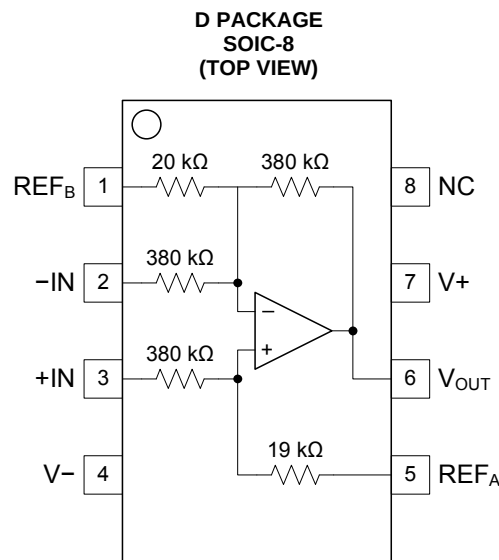
PARAMETER	TEST CONDITIONS	INA149			UNIT
		MIN	TYP	MAX	
GAIN					
Initial	V _{OUT} = 1.5 V to 3.5 V	1			V/V
Gain error	V _{OUT} = 1.5 V to 3.5 V	±0.005			%FSR
Gain	vs temperature, T _A = −40°C to +125°C	±1.5			ppm/°C
Nonlinearity		±0.0005			%FSR
OFFSET VOLTAGE					
Initial offset		350			μV
	vs temperature, T _A = −40°C to +125°C	3			μV/°C
	vs supply (PSRR), V _S = 4 V to 5 V	120			dB
INPUT					
Impedance	Differential	800			kΩ
	Common-mode	200			kΩ
Voltage range	Differential	1.5		3.5	V
	Common-mode	−20		25	V
Common-mode rejection	At dc, V _{CM} = −20 V to 25 V	100			dB
	vs temperature, T _A = −40°C to +125°C, at dc	100			dB
	At ac, 500 Hz, V _{CM} = 49 V _{PP}	100			dB
	At ac, 1 kHz, V _{CM} = 49 V _{PP}	90			dB
OUTPUT					
Voltage range		1.5		3.5	V
Short-circuit current		±15			mA
Capacitive load drive	No sustained oscillations	10			nF
OUTPUT NOISE VOLTAGE					
0.01 Hz to 10 Hz		20			μV _{PP}
10 kHz		550			nV/√Hz
DYNAMIC RESPONSE					
Small-signal bandwidth		500			kHz
Slew rate	V _{OUT} = 2 V _{PP} step	5			V/μs
Full-power bandwidth	V _{OUT} = 2 V _{PP}	32			kHz
Settling time	0.01%, V _{OUT} = 2 V _{PP} step	7			μs
POWER SUPPLY					
Voltage range		5			V
Quiescent current	V _S = 5 V	810			μA
	vs temperature, T _A = −40°C to +125°C	1			mA

THERMAL INFORMATION

THERMAL METRIC ⁽¹⁾		INA149	UNITS
		D (SOIC)	
		8 PINS	
θ_{JA}	Junction-to-ambient thermal resistance	110	°C/W
θ_{JCTop}	Junction-to-case (top) thermal resistance	57	
θ_{JB}	Junction-to-board thermal resistance	54	
ψ_{JT}	Junction-to-top characterization parameter	11	
ψ_{JB}	Junction-to-board characterization parameter	53	
θ_{JCbott}	Junction-to-case (bottom) thermal resistance	N/A	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

PIN CONFIGURATION



PIN DESCRIPTIONS

NAME	NO.	DESCRIPTION
–IN	2	Inverting input
+IN	3	Noninverting input
NC	8	No internal connection
REF _A	5	Reference input
REF _B	1	Reference input
V–	4	Negative power supply
V+	7	Positive power supply ⁽¹⁾
V _{OUT}	6	Output

(1) In this document, (V+) – (V–) is referred to as V_S.

TYPICAL CHARACTERISTICS

At $T_A = +25^\circ\text{C}$, $R_L = 2\text{ k}\Omega$ connected to ground, and $V_S = \pm 15\text{ V}$, unless otherwise noted.

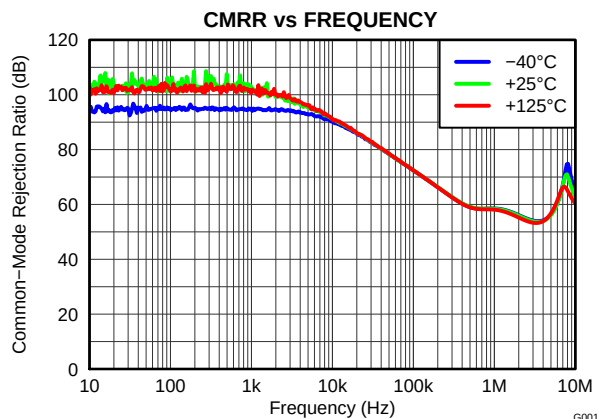


Figure 1.

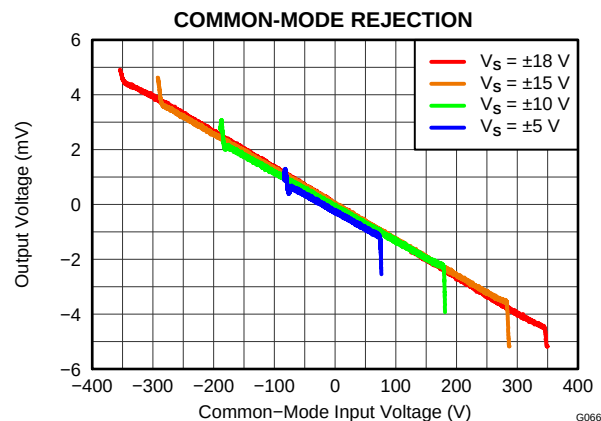


Figure 2.

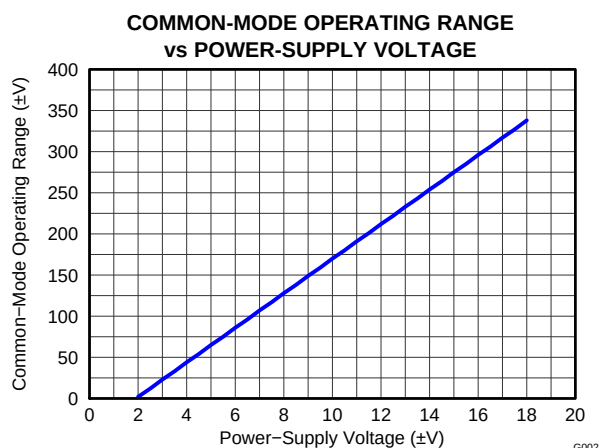


Figure 3.

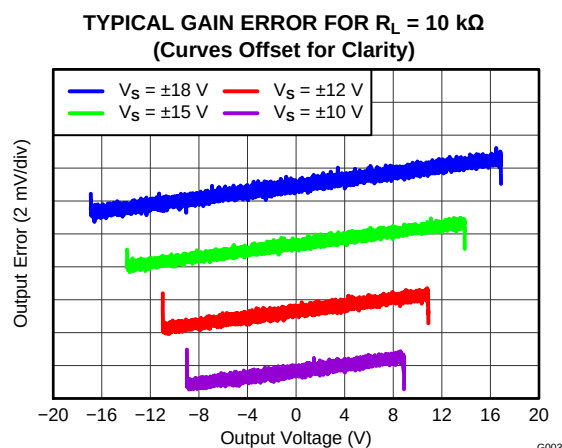


Figure 4.

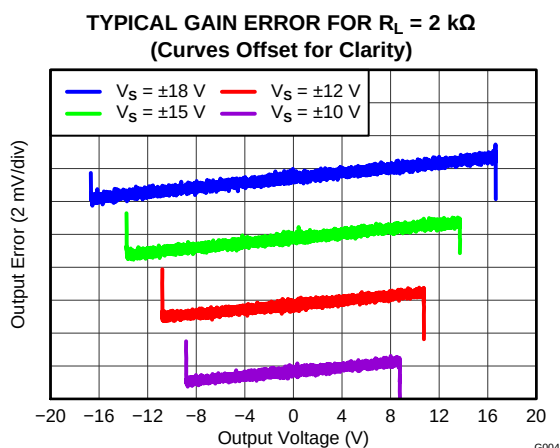


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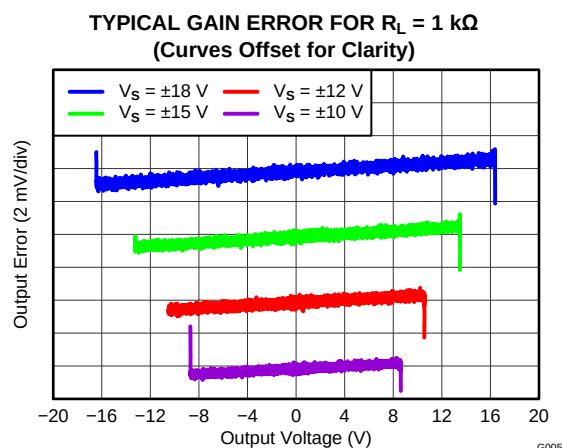


Figure 6.

TYPICAL CHARACTERISTICS (continued)

At $T_A = +25^\circ\text{C}$, $R_L = 2\text{ k}\Omega$ connected to ground, and $V_S = \pm 15\text{ V}$, unless otherwise noted.

TYPICAL GAIN ERROR FOR LOW SUPPLY VOLTAGES (Curves Offset for Clarity)

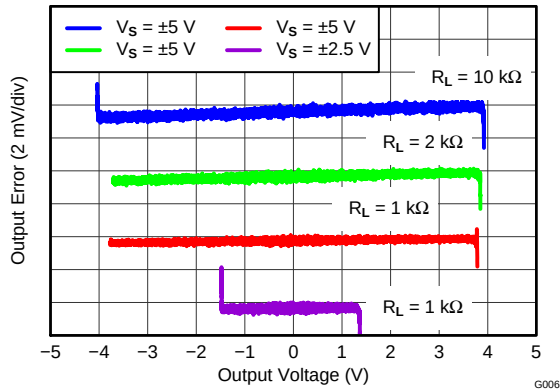


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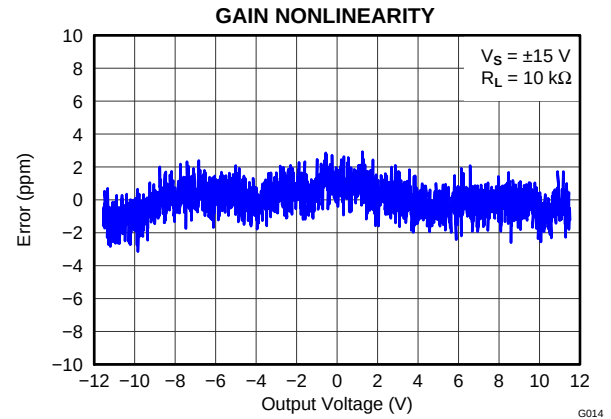


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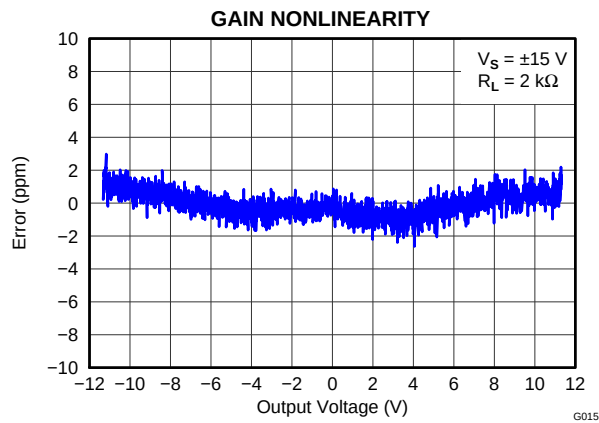


Figure 9.

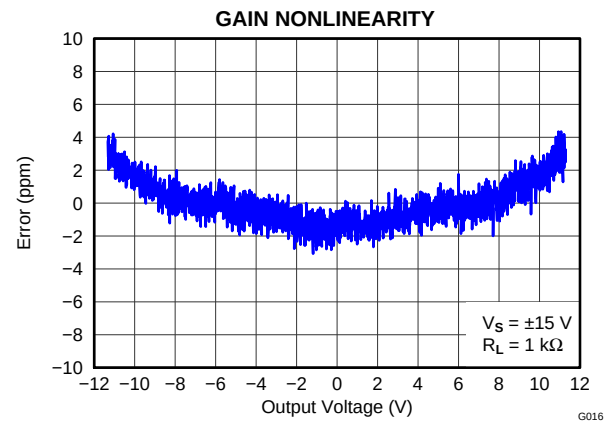


Figure 10.

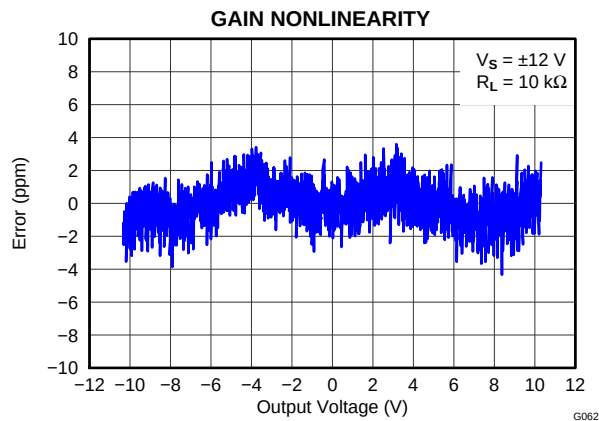


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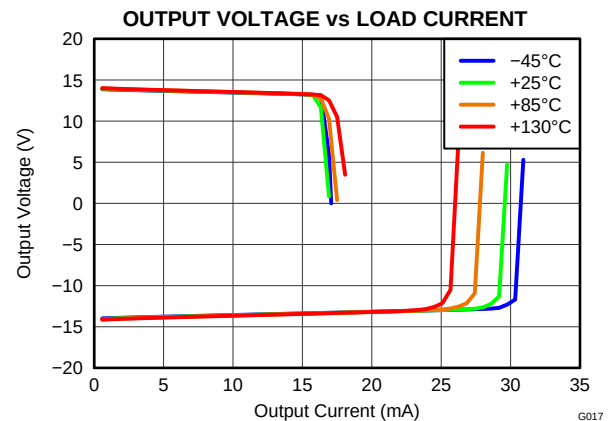


Figure 12.

TYPICAL CHARACTERISTICS (continued)

At $T_A = +25^\circ\text{C}$, $R_L = 2\text{ k}\Omega$ connected to ground, and $V_S = \pm 15\text{ V}$, unless otherwise noted.

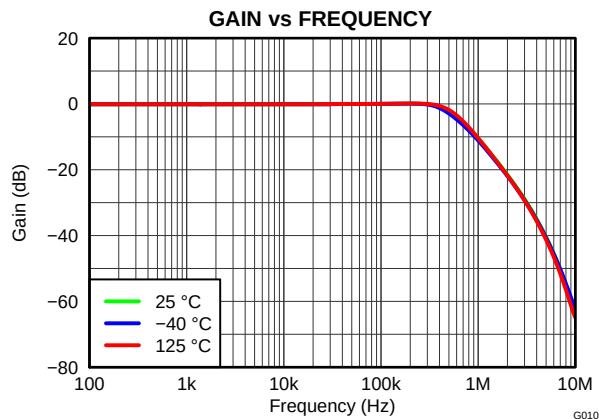


Figure 13.

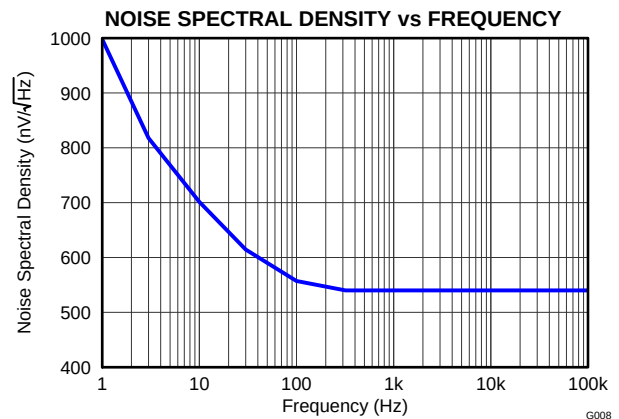


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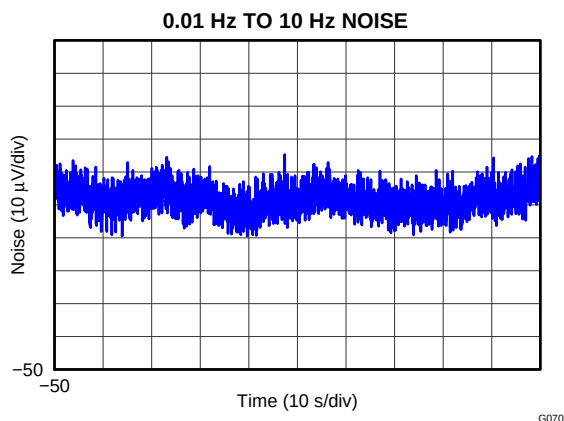


Figure 15.

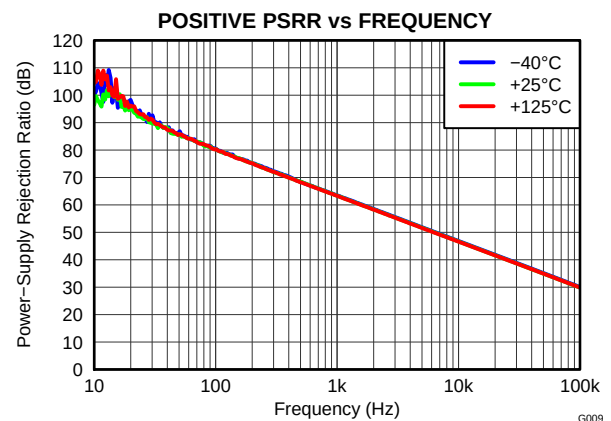


Figure 16.

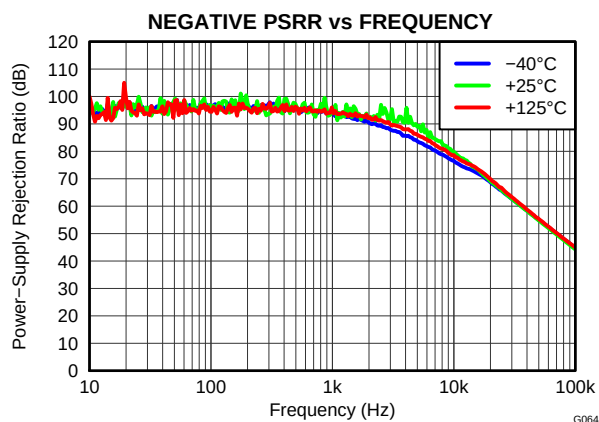


Figure 17.

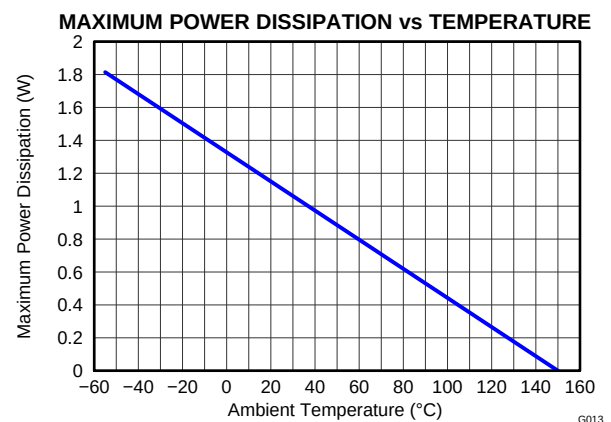


Figure 18.

TYPICAL CHARACTERISTICS (continued)

At $T_A = +25^\circ\text{C}$, $R_L = 2\text{ k}\Omega$ connected to ground, and $V_S = \pm 15\text{ V}$, unless otherwise noted.

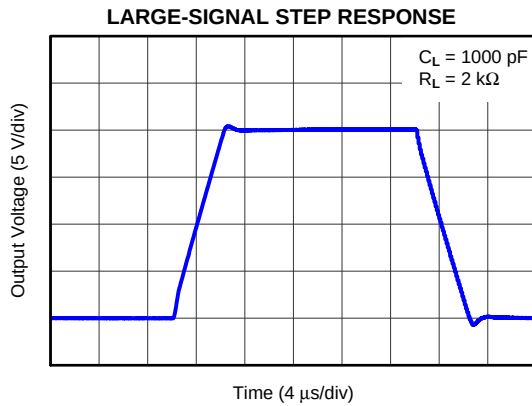


Figure 19.

G011

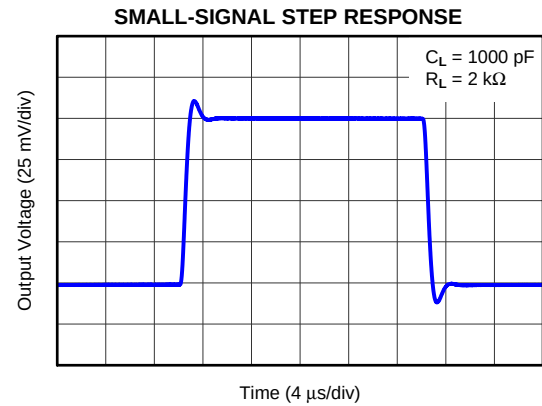


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G012

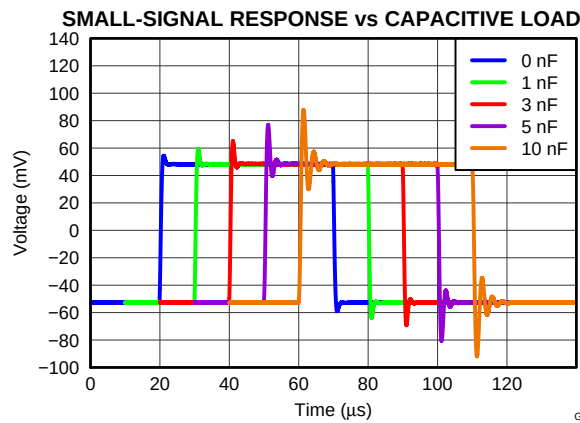


Figure 21.

G065

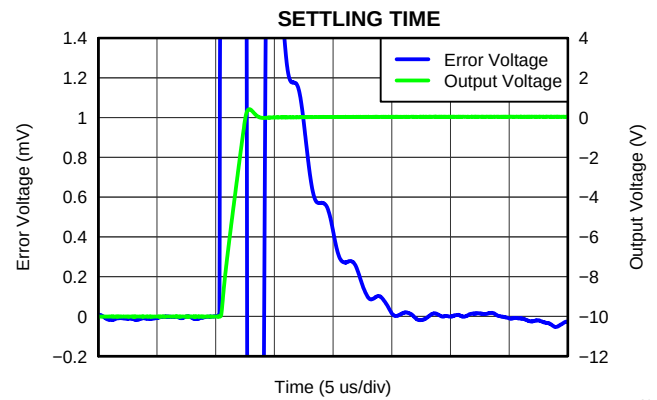


Figure 22.

G018

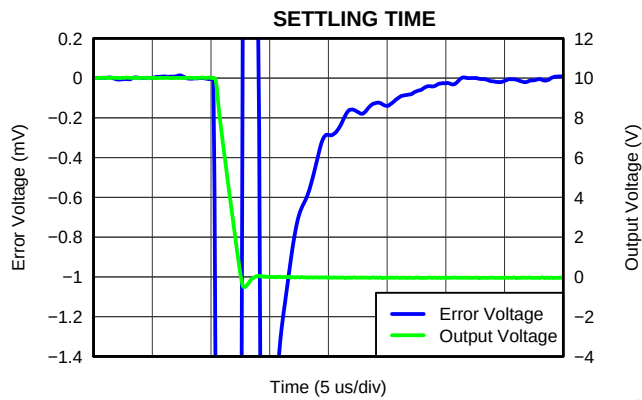


Figure 23.

G063

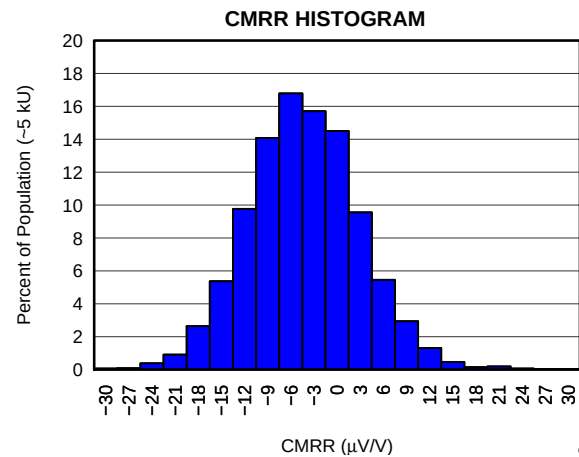


Figure 24.

G019

TYPICAL CHARACTERISTICS (continued)

At $T_A = +25^\circ\text{C}$, $R_L = 2\text{ k}\Omega$ connected to ground, and $V_S = \pm 15\text{ V}$, unless otherwise noted.

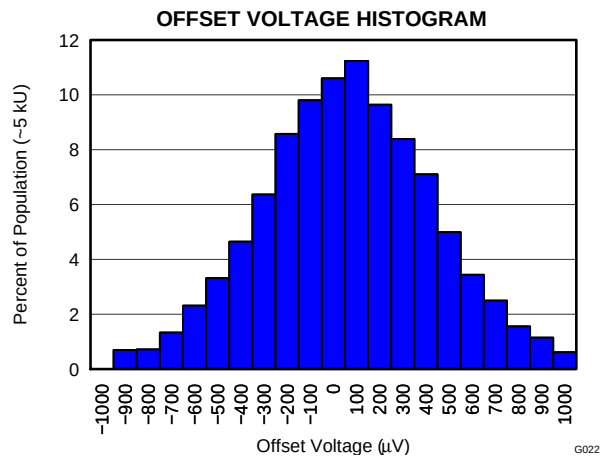


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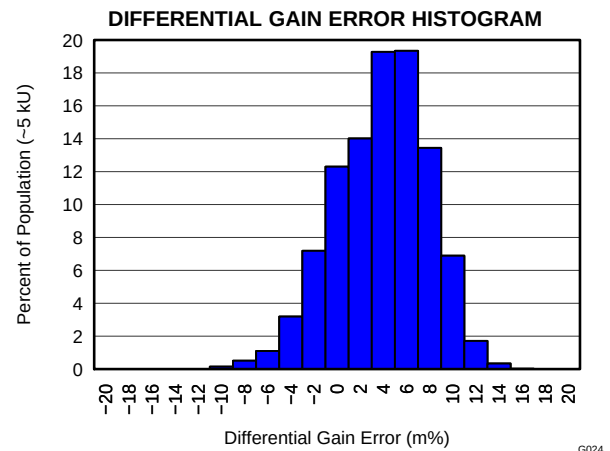


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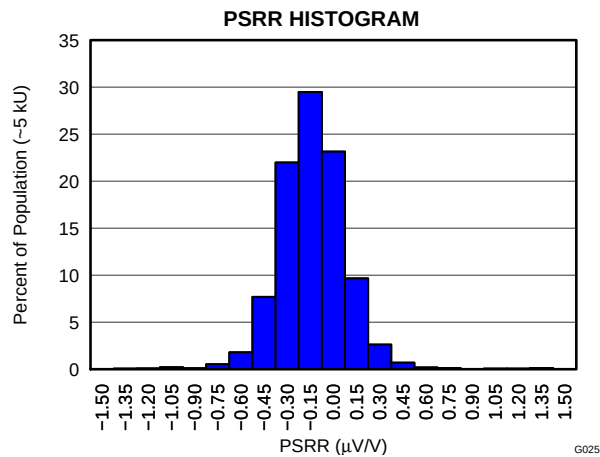


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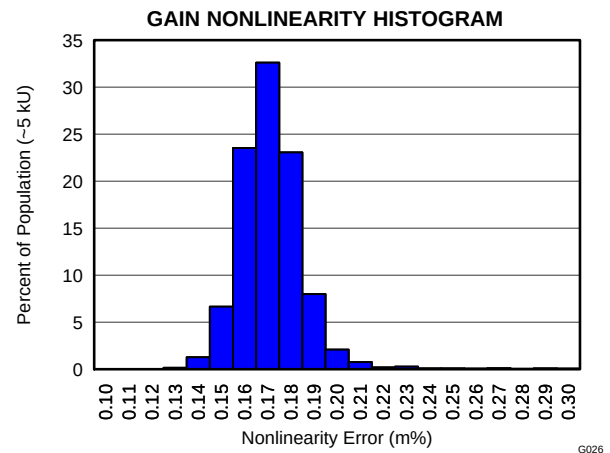


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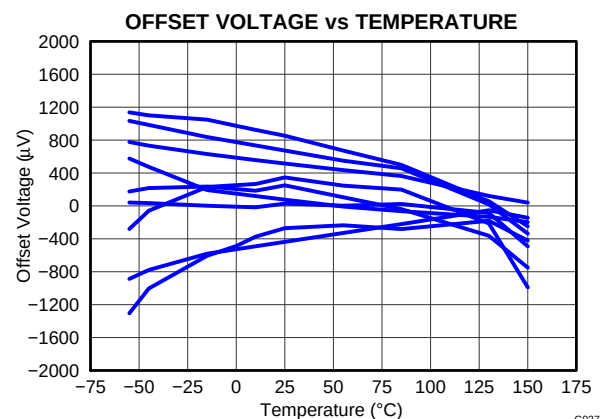


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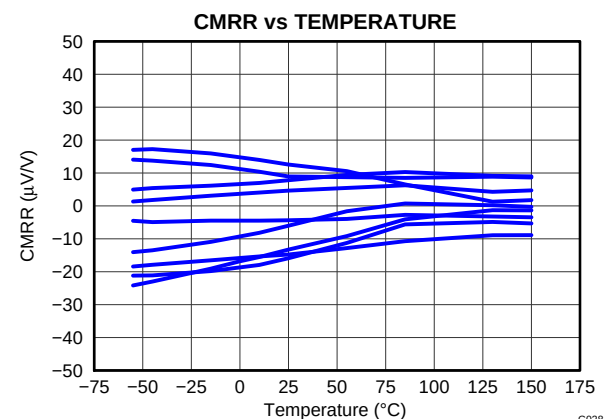


Figure 30.

TYPICAL CHARACTERISTICS (continued)

At $T_A = +25^\circ\text{C}$, $R_L = 2\text{ k}\Omega$ connected to ground, and $V_S = \pm 15\text{ V}$, unless otherwise noted.

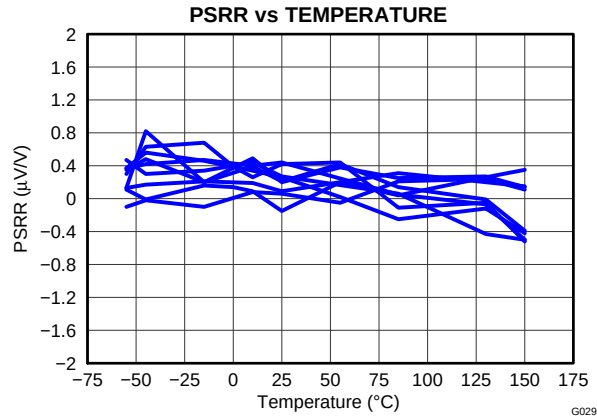


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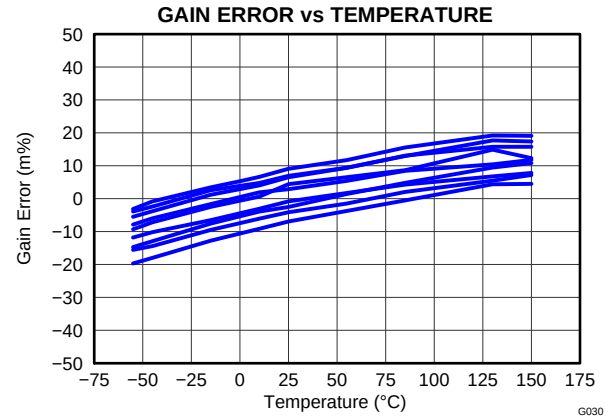


Figure 32.

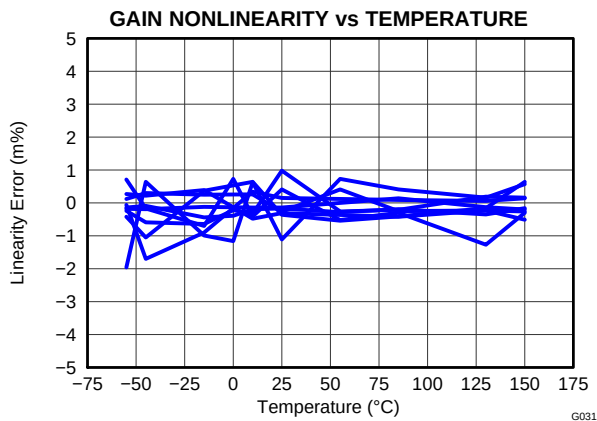


Figure 33.

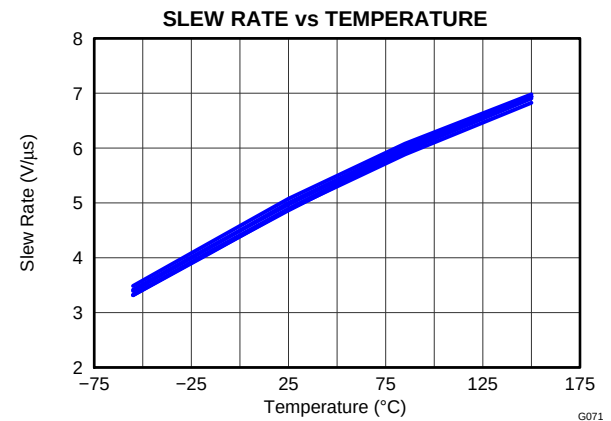


Figure 34.

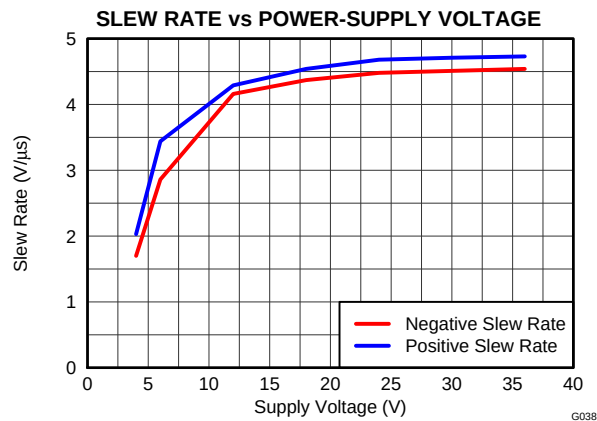


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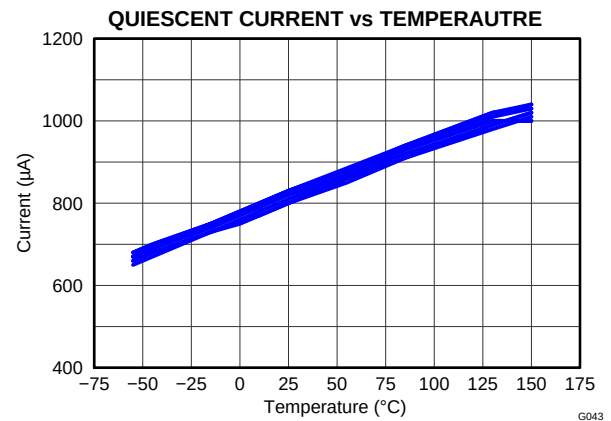


Figure 36.

TYPICAL CHARACTERISTICS (continued)

At $T_A = +25^\circ\text{C}$, $R_L = 2\text{ k}\Omega$ connected to ground, and $V_S = \pm 15\text{ V}$, unless otherwise noted.

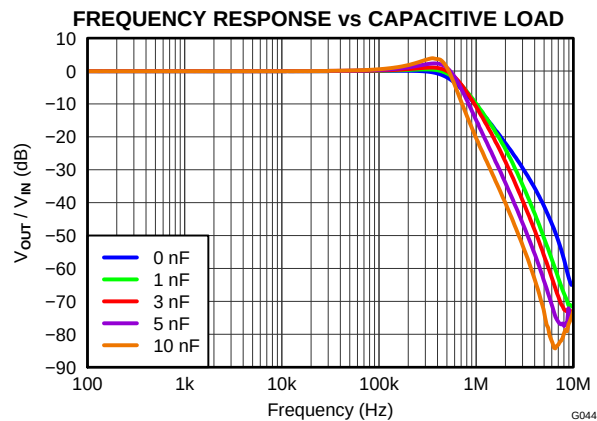


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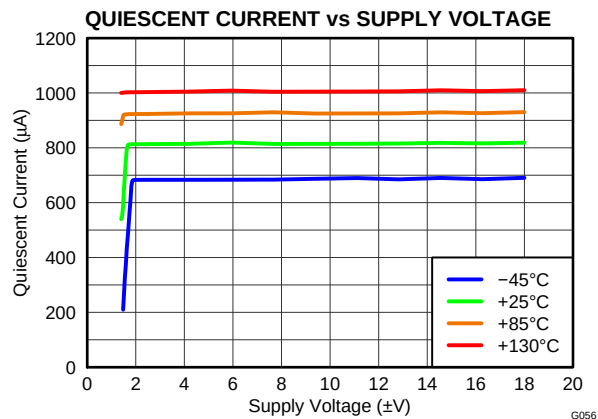


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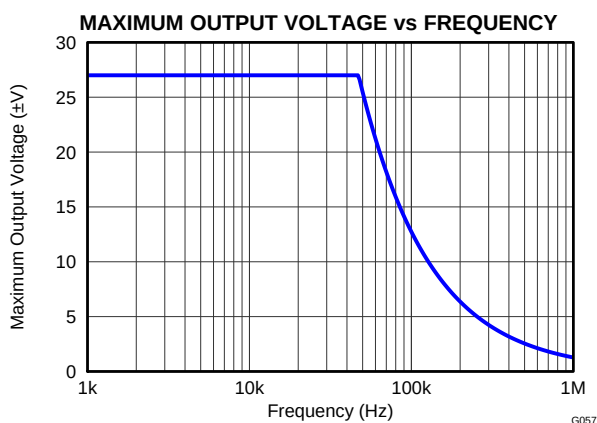


Figure 39.

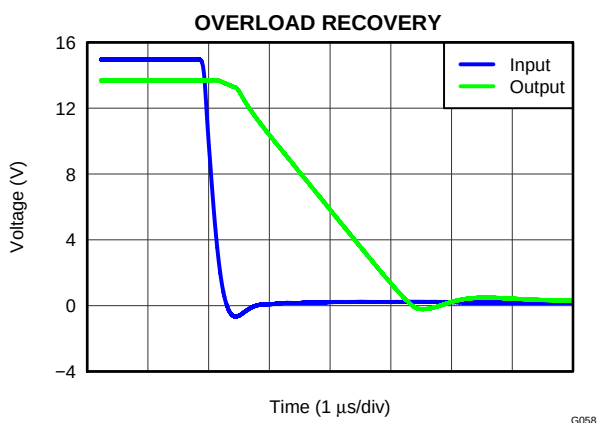


Figure 40.

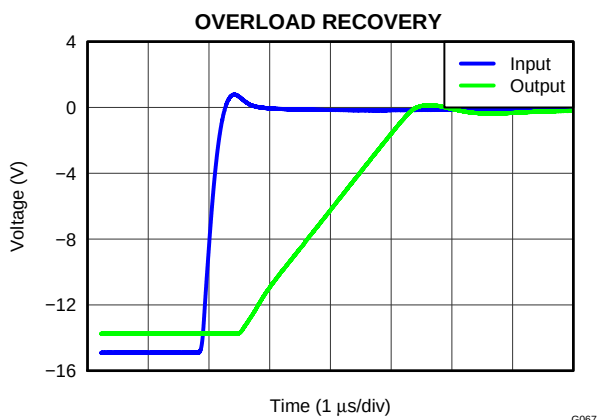


Figure 41.

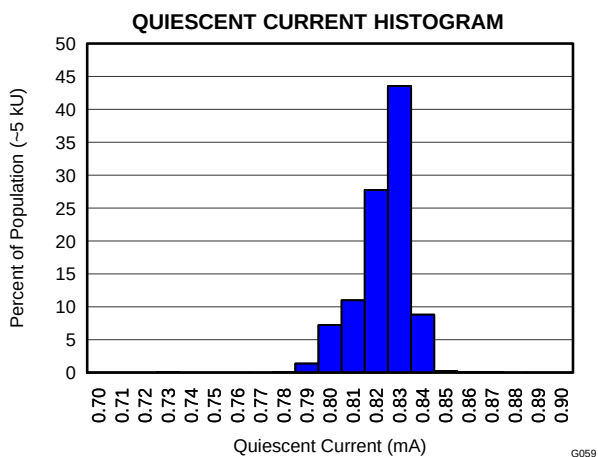


Figure 42.

APPLICATION INFORMATION

BASIC INFORMATION

Figure 43 shows the basic connections required for dual-supply operation. Applications with noisy or high-impedance power-supply lines may require decoupling capacitors placed close to the device pins. The output voltage is equal to the differential input voltage between pins 2 and 3. The common-mode input voltage is rejected. Figure 44 shows the basic connections required for single-supply operation.

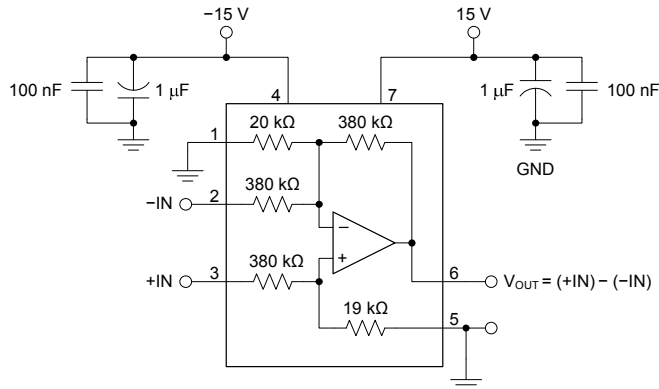


Figure 43. Basic Power and Signal Connections for Dual-Supply Operation

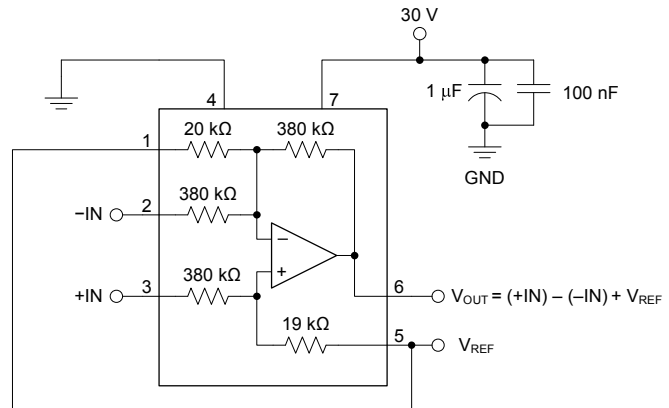


Figure 44. Basic Power and Signal Connections for Single-Supply Operation

TRANSFER FUNCTION

Most applications use the INA149 as a simple unity-gain difference amplifier. The transfer function is given in Equation 1:

$$V_{OUT} = (+IN) - (-IN) \quad (1)$$

Some applications, however, apply voltages to the reference terminals (REF_A and REF_B). The complete transfer function is given in Equation 2:

$$V_{OUT} = (+IN) - (-IN) + 20 \times REF_A - 19 \times REF_B \quad (2)$$

COMMON-MODE RANGE

The high common-mode range of the INA149 is achieved by dividing down the input signal with a high precision resistor divider. This resistor divider brings both the positive input and the negative input within the input range of the internal operational amplifier. This input range depends on the supply voltage of the INA149.

Both Figure 2 and Figure 3 can be used to determine the maximum common-mode range for a specific supply voltage. The maximum common-mode range can also be calculated by ensuring that both the positive and the negative input of the internal amplifier are within 1.5 V of the supply voltage.

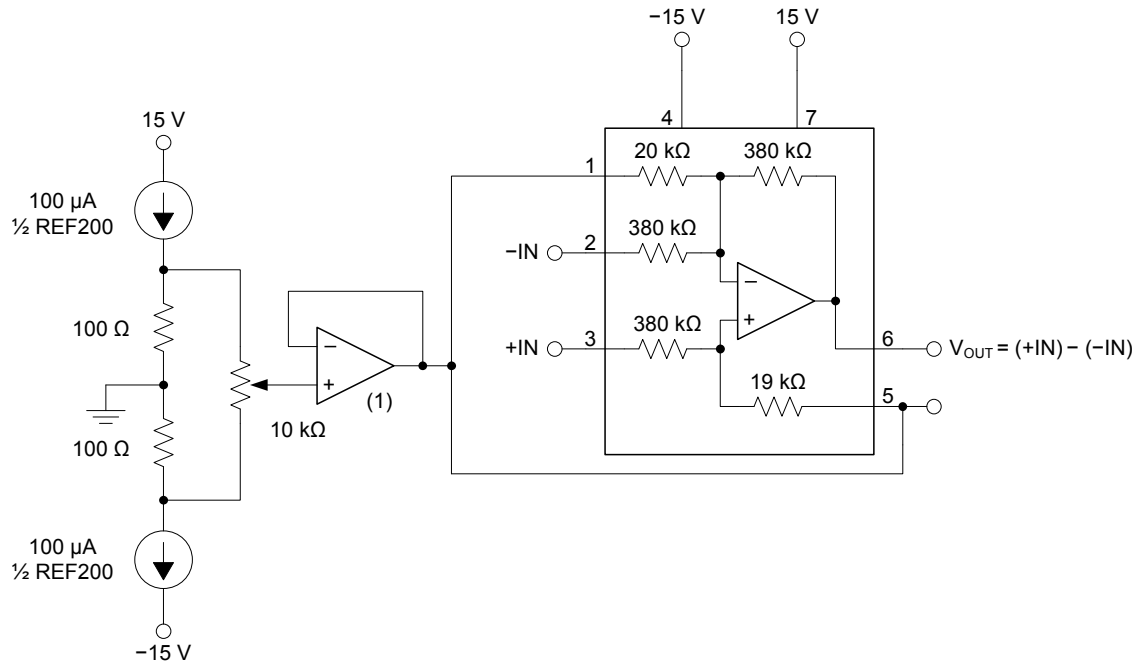
In case the voltage at the inputs of the internal amplifier exceeds the supply voltage, the internal ESD diodes start conducting current. This current must be limited to 10 mA to make sure not to exceed the absolute maximum ratings for the device.

COMMON-MODE REJECTION

Common-mode rejection (CMR) of the INA149 depends on the input resistor network, which is laser-trimmed for accurate ratio matching. To maintain high CMR, it is important to have low source impedance driving the two inputs. A 75-Ω resistance in series with pins 2 or 3 decreases the common-mode rejection ratio (CMRR) from 100 dB (typical) to 74 dB.

Resistance in series with the reference pins also degrades CMR. A 4-Ω resistance in series with pins 1 or 5 decreases CMRR from 100 dB to 74 dB.

Most applications do not require trimming. Figure 45 shows an optional circuit that may be used for trimming offset voltage and common-mode rejection.



(1) The [OPA171](#) (a 36-V, low-power, RRO, general-purpose operational amplifier) can be used for this application.

Figure 45. Offset Voltage Trim Circuit

MEASURING CURRENT

The INA149 can be used to measure a current by sensing the voltage drop across a series resistor, R_S . Figure 46 shows the INA149 used to measure the supply currents of a device under test.

The sense resistor imbalances the input resistor matching of the INA149, thus degrading its CMR. Also, the input impedance of the INA149 loads R_S , causing gain error in the voltage-to-current conversion. Both of these errors can be easily corrected.

The CMR error can be corrected with the addition of a compensation resistor (R_C), equal to the value of R_S , as shown in Figure 46. If R_S is less than 5 Ω , degradation in the CMR is negligible and R_C can be omitted. If R_S is larger than approximately 1 k Ω , trimming R_C may be required to achieve greater than 90-dB CMR. This error is caused by the INA149 input impedance mismatch.

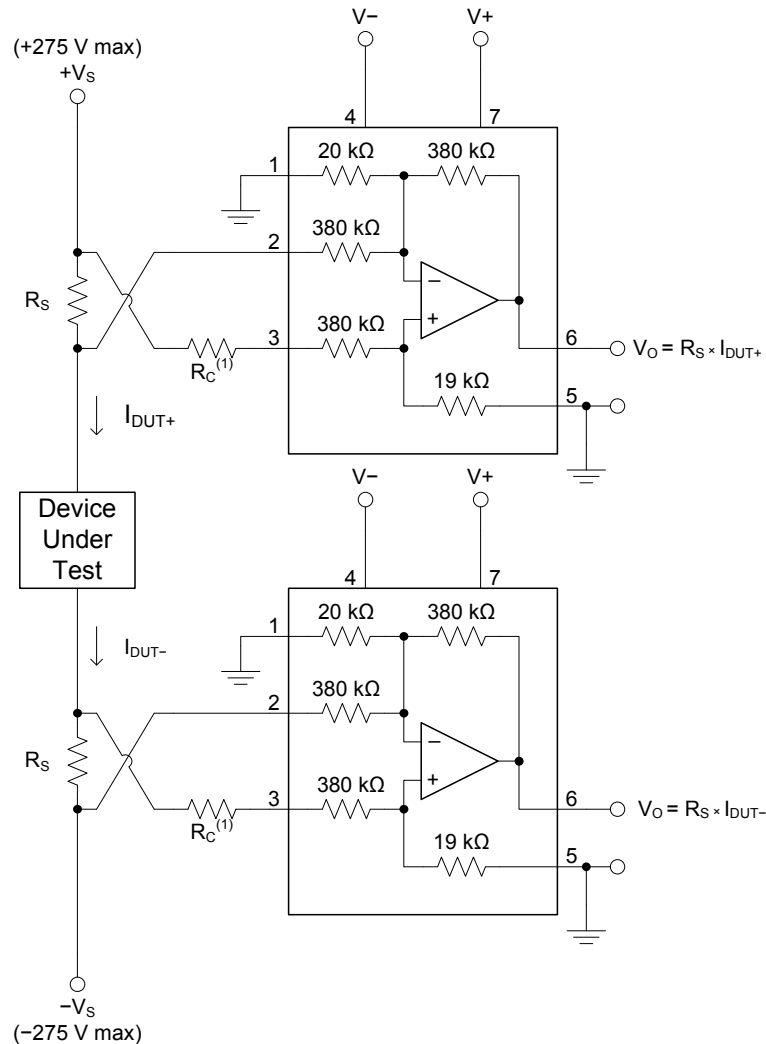


Figure 46. Measuring Supply Currents of a Device Under Test

If R_S is more than approximately 50 Ω , the gain error is greater than the 0.02% specification of the INA149. This gain error can be corrected by slightly increasing the value of R_S . The corrected value (R_S') can be calculated by $R_S' = R_S \times 380 \text{ k}\Omega / (380 \text{ k}\Omega - R_S)$ (3)

Example: For a 1-V/mA transfer function, the nominal, uncorrected value for R_S would be 1 k Ω . A slightly larger value ($R_S' = 1002.6 \Omega$), compensates for the gain error as a result of loading.

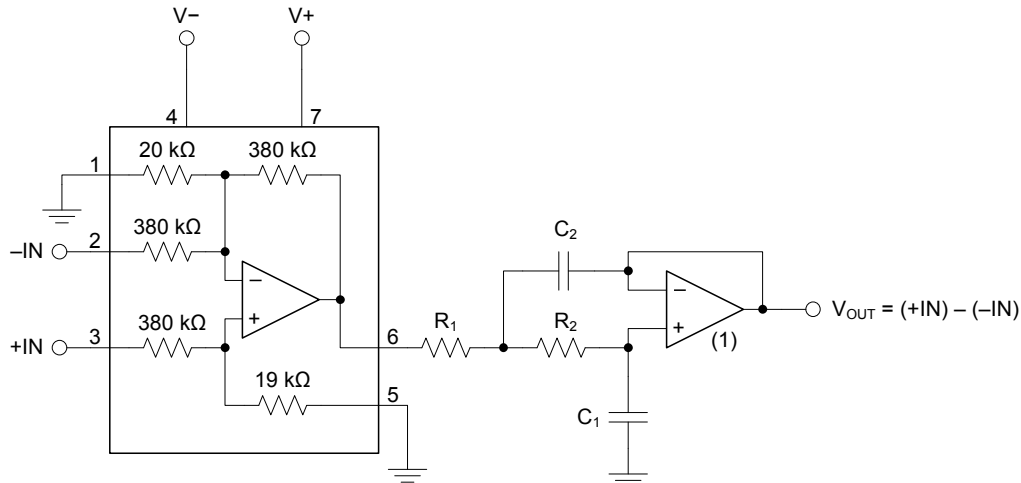
The 380-k Ω term in the equation for R_S' has a tolerance of 25%, thus sense resistors above approximately 400 Ω may require trimming to achieve gain accuracy better than 0.02%.

NOISE PERFORMANCE

The wideband noise performance of the INA149 is dominated by the internal resistor network. The thermal or *Johnson noise* of these resistors measures approximately 550 nV/√Hz. The internal op amp contributes virtually no excess noise at frequencies above 100 Hz.

Many applications may be satisfied with less than the full 500-kHz bandwidth of the INA149. In these cases, the noise can be reduced with a low-pass filter on the output. The two-pole filter shown in Figure 47 limits bandwidth and reduces noise. Because the INA149 has a 1/f noise corner frequency of approximately 100 Hz, a cutoff frequency below 100 Hz does not further reduce noise.

Component values for different filter frequencies are shown in Table 1.



(1) For most applications, the OPA171 can be used as an operational amplifier. For directly driving successive-approximation register (SAR) data converters, the OPA140 is a good choice.

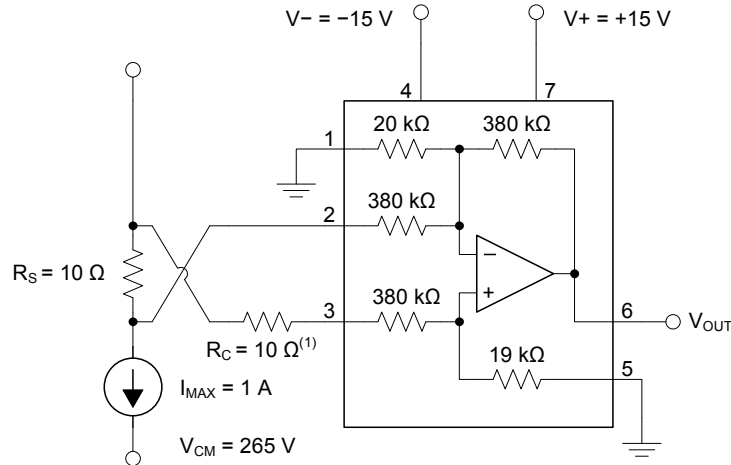
Figure 47. Output Filter for Noise Reduction

Table 1. Components Values for Different Filter Bandwidths

BUTTERWORTH LOW-PASS ($f_{-3\text{ dB}}$)	OUTPUT NOISE (mV _{PP})	R ₁	R ₂	C ₁	C ₂
200 kHz	1.8	No filter			
100 kHz	1.1	11 kΩ	11.3 kΩ	100 pF	200 pF
10 kHz	0.35	11 kΩ	11.3 kΩ	1 nF	2 nF
1 kHz	0.11	11 kΩ	11.3 kΩ	10 nF	20 nF
100 Hz	0.05	11 kΩ	11.3 kΩ	0.1 μF	0.2 μF

ERROR BUDGET ANALYSIS

The following error budget analysis demonstrates the importance of a high common-mode rejection ratio when measuring small differential signals in the presence of high common-mode voltages. Figure 48 shows a typical current measurement application.



(1) See the [Measuring Current](#) section for details about R_C .

Figure 48. Typical Current Measurement Application

The maximum current through the shunt resistor (R_S) is 1 A and generates a full-scale voltage drop of 10 V. All error sources in this calculation are shown in relation to this full-scale voltage. The common-mode voltage in this scenario is 265 V and the temperature range is from room temperature (+25°C) to +85°C. Table 2 shows the dominant error sources for the INA149 and a competitor device.

Table 2. Error Budget Analysis

ERROR SOURCE	INA149	COMPETIOR A	ERROR (ppm of FS)	
			INA149	COMPETITOR A
Accuracy, T _A = +25°C				
Initial gain error	0.02% FS	0.05% FS	200	500
Offset voltage	1100 μV	1000 μV	110	100
Common mode	265 V/90 dB = 8380 μV	265 V/77 dB = 37432 μV	838	3743
Total acuracy error			1148	4343
Temperature drift				
Gain	10 ppm/°C × 60°C	10 ppm/°C × 60°C	600	600
Offset voltage	10 μV/°C × 60°C	20 μV/°C × 60°C	60	120
Total drift error			660	720
Total error			1808	5063

If a smaller shunt resistor is used, the full-scale voltage drop is also smaller. A shunt resistor of 1 Ω causes a 1-V voltage drop with a current of 1 A flowing through it. The error of 1808 ppm for a full-scale voltage of 10 V becomes 18080 ppm (1.6%) for a full-scale voltage of only 1 V.

This example demonstrates that the dominate source of error, even over temperature, comes from the CMRR specification of the devices. The common-mode error is 46% of the total error for the INA149 and 74% of the total error for the competitor device.

BATTERY CELL VOLTAGE MONITOR

The INA149 can be used to measure the voltages of single cells in a stacked battery pack. Figure 49 shows an examples for such an application.

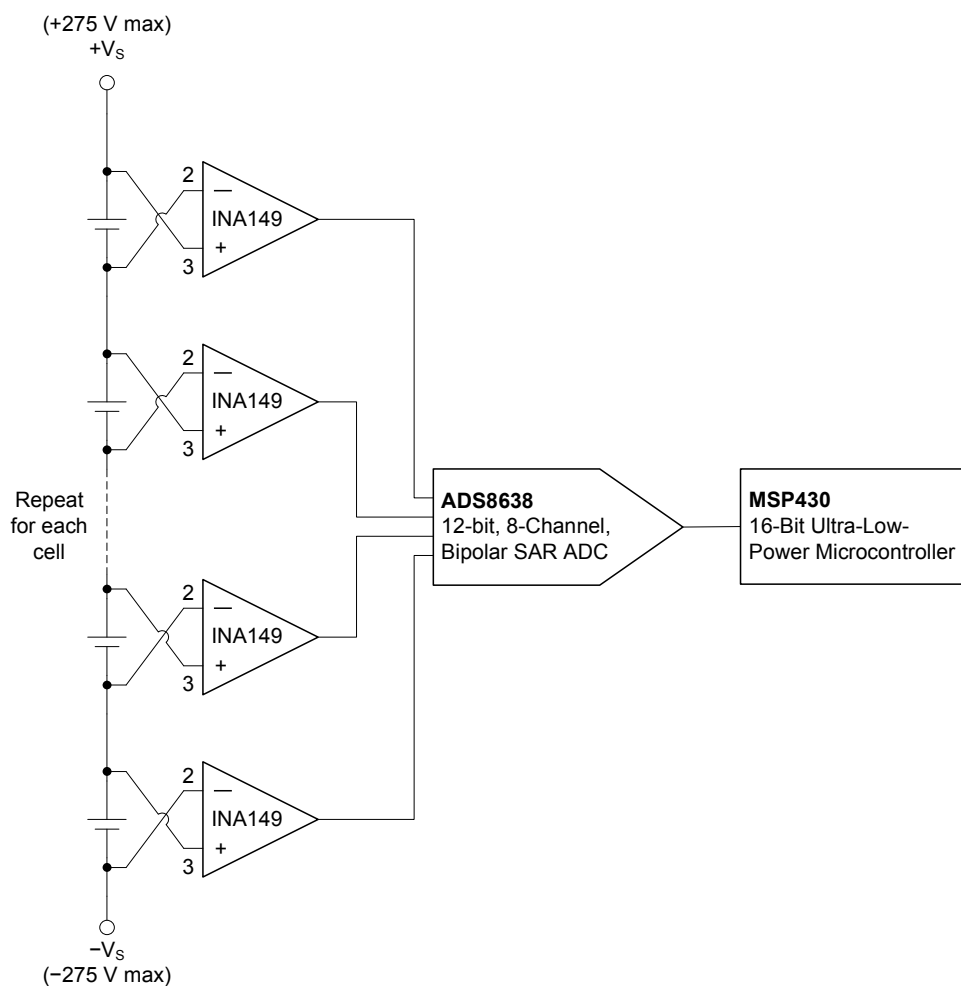


Figure 49. Battery Cell Voltage Monitor

REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (November 2011) to Revision B	Page
• Changed package marking data in Package/Ordering Information table	2

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4)	Samples
INA149AID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 149A	Samples
INA149AIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 149A	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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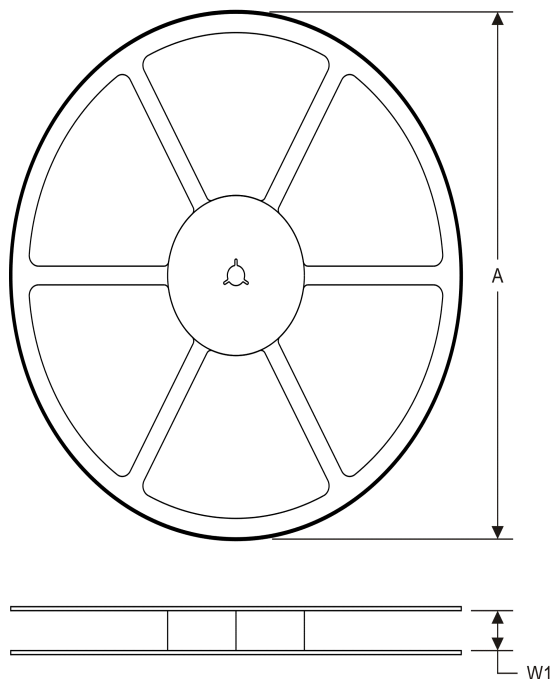
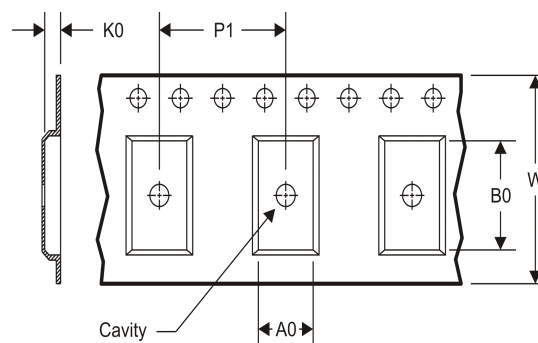
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF INA149 :

-
- Enhanced Product: [INA149-EP](#)

NOTE: Qualified Version Definitions:

- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION
REEL DIMENSIONS

TAPE DIMENSIONS


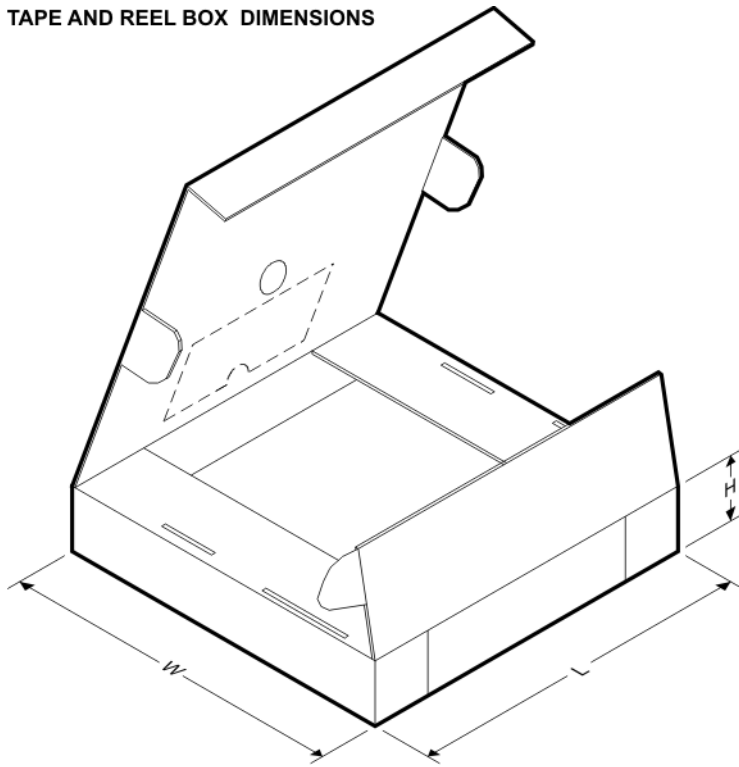
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA149AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
INA149AIDR	SOIC	D	8	2500	367.0	367.0	35.0



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

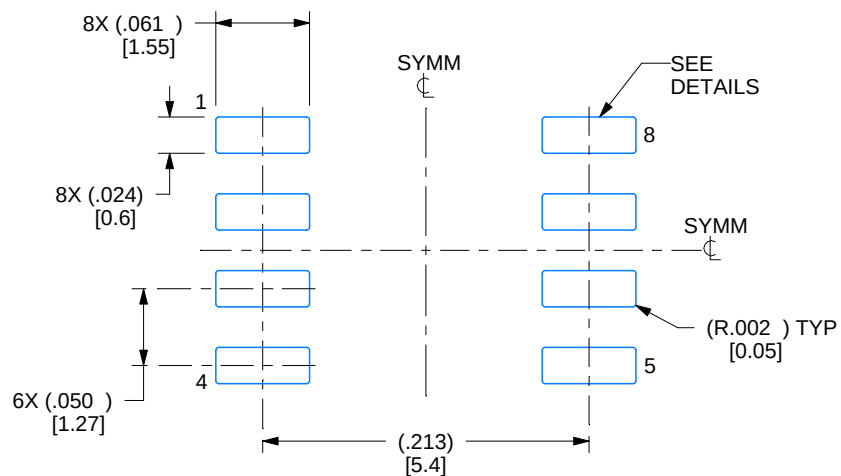


1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

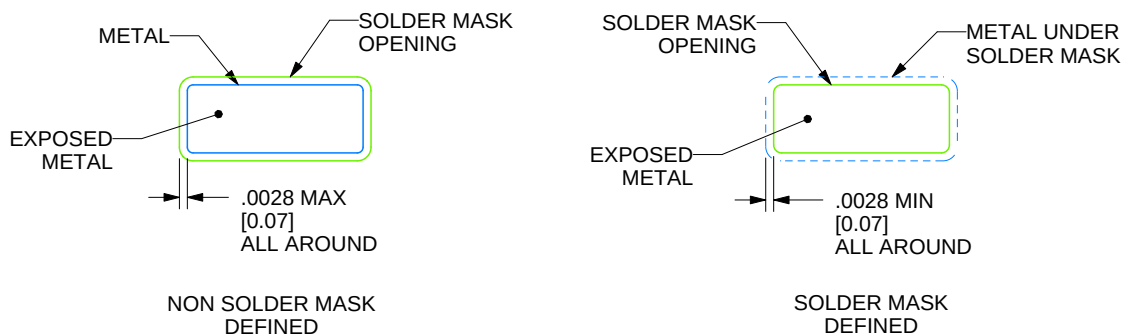
D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

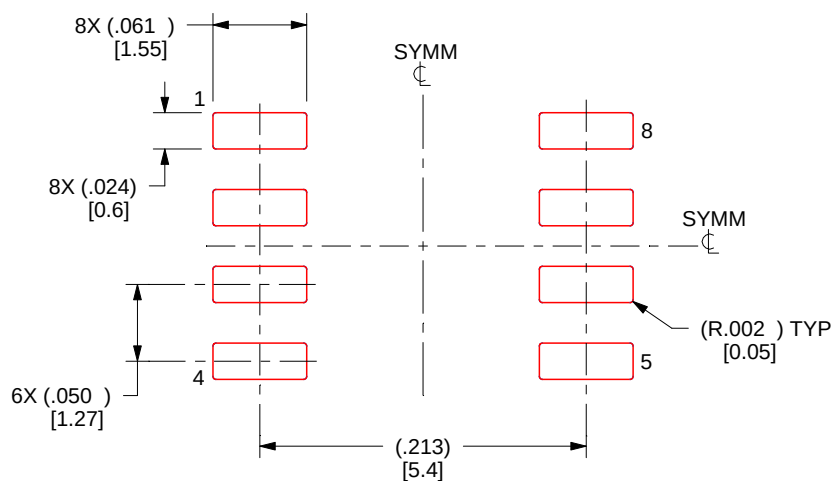
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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